

# METHOD AND DEVICE FOR CHEMICAL VAPOR PHASE GROWTH OF TANTALUM OXIDE FILM

Patent number: JP2250970  
Publication date: 1990-10-08  
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Classification:  
- international: C23C16/40; H01L21/31; H01L27/04  
- european:  
Application number: JP19890071206 19890322  
Priority number(s):

Also published as:

EP0388957 (A2)  
EP0388957 (A3)

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## Abstract of JP2250970

**PURPOSE:** To grow a dense tantalum oxide film in which impurities, pinholes and a leakage current are reduced by using gaseous TaCl<sub>5</sub> and gaseous N<sub>2</sub>O as the raw gaseous materials and causing a plasma chemical reaction.

**CONSTITUTION:** Gaseous TaCl<sub>5</sub> is introduced into a reaction chamber 112 from a vaporization chamber 106, and N<sub>2</sub>O is introduced into the reaction chamber 112 through a valve 116. A high frequency power source 109 is turned on, and a plasma chemical reaction is caused between the introduced TaCl<sub>5</sub> and N<sub>2</sub>O to form a tantalum oxide film on the surface of a silicon substrate of a wafer 110. The quality of the film can be improved by introducing H<sub>2</sub> when the film is formed. The inside of the reaction chamber 112 is cleansed by the plasma chemical reaction using a gaseous fluorine-based halogen compd., and the quality, thickness, etc., of the tantalum oxide film are secured with good reproducibility.

